

Title (en)

METHOD FOR FORMING A UNIFORM NETWORK OF SEMICONDUCTOR ISLANDS ON AN INSULATING SUBSTRATE

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES NETZES AUS REGELMÄSSIG GEORDNETEN HALBLEITER-INSELN AUF EINEM ISOLIERENDEN SUBSTRAT

Title (fr)

PROCEDE DE FORMATION D'UN RESEAU REGULIER D'ILOTS SEMI-CONDUCTEURS SUR UN SUBSTRAT ISOLANT

Publication

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Application

EP 98962497 A 19981217

Priority

- FR 9802769 W 19981217
- FR 9716158 A 19971219

Abstract (en)

[origin: FR2772984A1] An array of semiconductor material islands (124) is formed on uniformly distributed nucleation seeds (122, 122a) deposited on an insulating material (112) using a distribution layer (116) of material having a regular molecular structure. Independent claims are also included for the following: (i) production of a quantum structure of Coulomb blocking type having an array of semiconductor islands formed by the above process; and (ii) a Coulomb blocking type electronic device having electron sources separated by a collection of nano-size semiconductor islands regularly spaced on an insulating substrate.

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IPC 8 full level

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Citation (search report)

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